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- Members of the Texas Instruments (TI™)
 Widebus™ Family
- UBT[™] (Universal Bus Transceiver)
 Combines D-Type Latches and D-Type
 Flip-Flops for Operation in Transparent,
 Latched, Clocked, or Clock-Enabled Mode
- Translate Between GTLP Signal Levels and LVTTL Logic Levels
- Support Mixed-Mode (3.3 V and 5 V) Signal Operation on A-Port and Control Inputs
- B-Port Transition Time Optimized for Distributed Backplane Loads
- I_{off} Supports Partial-Power-Down Mode Operation

- Bus Hold on A-Port Inputs Eliminates the Need for External Pullup/Pulldown Resistors
- Distributed V_{CC} and GND Pins Minimize High-Speed Switching Noise
- ESD Protection Exceeds JESD 22
 - 2000-V Human-Body Model (A114-A)
 - 200-V Machine Model (A115-A)
 - 1000-V Charged-Device Model (C101)
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- Package Options Include Plastic Shrink Small-Outline (DL), and Thin Shrink Small-Outline (DGG) Packages

NOTE: For tape and reel order entry:
The DGGR package is abbreviated to GR.

description

The SN74GTLPH16612 is a medium-drive, 18-bit UBT (universal bus transceiver) that provides LVTTL-to-GTLP and GTLP-to-LVTTL signal-level translation. It allows for transparent, latched, clocked, or clock-enabled modes of data transfer. This device provides a high-speed interface between cards operating at LVTTL logic levels and backplanes operating at GTLP signal levels. High-speed (about two times faster than standard LVTTL or TTL) backplane operation is a direct result of the reduced output swing (<1 V), reduced input threshold levels, and OEC™ (output edge control). These improvements minimize bus settling time and have been designed and tested using several backplane models.

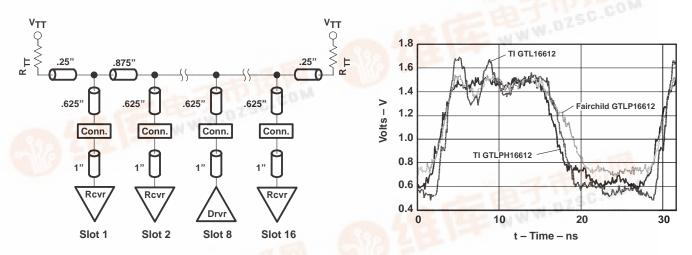


Figure 1. Test Backplane Model With Output Waveform Results

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description (continued)

Figure 1 shows actual device output waveforms using a synchronous clock at 75 MHz. The test backplane is a 16-slot, 14-inch board with loaded impedance of $33\,\Omega$. V_{TT} is 1.5 V, V_{REF} is 1 V, and R_{TT} pullup resistor is 50 Ω . The driver is in slot 8, with receivers in alternate slots 1, 3, 5, 7, 10, 12, 14, and 16. Receiver slot 1 signals are shown. The signal becomes progressively worse as the receiver moves closer to the driver or the spacing between receiver cards is reduced. The clock is independent of the data and the system clock frequency is limited by the backplane flight time to about 80 MHz to 90 MHz. This frequency can be increased even more (30% to 40%) if the clock is generated and transmitted together with the data from the driver card (source synchronous).

The SN74GTLPH16612 is a medium-drive (34 mA), 18-bit universal bus transceiver, containing D-type latches and D-type flip-flops to allow data flow in transparent, latched, clocked, and clock-enabled modes. This UBT can replace any of the functions shown in Table 1.

FUNCTION	8 BIT	9 BIT	10 BIT	16 BIT	18 BIT	
Transceiver	'245, '623, '645	'863	'861	'16245, '16623	'16863	
Buffer/driver	'241, '244, '541		'827	'16241, '16244, '16541	'16825	
Latched transceiver	'543			'16543	'16472	
Latch	'373, '573	'843	'841	'16373	'16843	
Registered transceiver	'646, '652			'16646, '16652	'16474	
Flip-flop	'374, '574		'821	'16374		
Standard UBT					'16500, '16501	
Universal bus driver					'16835	
Registered transceiver with CLK enable	'2952			'16470, '16952		
Flip-flop with CLK enable	'377	'823			'16823	
Standard UBT with CLK enable					'16600, '16601	
SN74GTLPH16612 UBT replaces all above functions						

Table 1. SN74GTLPH16612 UBT Replacement Functions

GTLP is a TI derivative of the Gunning transceiver logic (GTL) JEDEC standard JESD 8-3. The ac specification of the SN74GTLPH16612 is given only at the preferred higher noise-margin GTLP, but this device can be used at either GTL ($V_{TT} = 1.2 \text{ V}$ and $V_{REF} = 0.8 \text{ V}$) or GTLP ($V_{TT} = 1.5 \text{ V}$ and $V_{REF} = 1 \text{ V}$) signal levels.

The B port normally operates at GTLP levels, while the A-port and control inputs are compatible with LVTTL logic levels and are 5-V tolerant. V_{RFF} is the reference input voltage for the B port.

To improve signal integrity, the SN74GTLPH16612 B-port output transition time is optimized for distributed backplane loads.

V_{CC} (5 V) supplies the internal and GTLP circuitry, while V_{CC} (3.3 V) supplies the LVTTL output buffers.

To ensure the high-impedance state during power up or power down, \overline{OE} should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

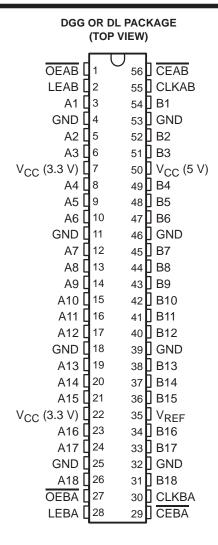
Active bus-hold circuitry holds unused or undriven LVTTL inputs at a valid logic state. Use of pullup or pulldown resistors with the bus-hold circuitry is not recommended.

This device is fully specified for partial-power-down applications using I_{off}. The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

The SN74GTLPH16612 is characterized for operation from -40°C to 85°C.



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functional description

Data flow in each direction is controlled by the clock-enables (CEAB and CEBA), latch-enables (LEAB and LEBA), clock (CLKAB and CLKBA), and output-enables (OEAB and OEBA).

For A-to-B data flow, when $\overline{\text{CEAB}}$ is low, the device operates on the low-to-high transition of CLKAB for the flip-flop and on the high-to-low transition of LEAB for the latch path, i.e., if $\overline{\text{CEAB}}$ and LEAB are low, the A data is latched, regardless of the state of CLKAB (high or low) and if LEAB is high, the device is in transparent mode. When $\overline{\text{OEAB}}$ is low, the outputs are active. When $\overline{\text{OEAB}}$ is high, the outputs are in the high-impedance state.

The data flow for B to A is similar to A to B, except that $\overline{\text{CEBA}}$, $\overline{\text{OEBA}}$, LEBA, and CLKBA are used.

FUNCTION TABLE[†]

	INPUTS					MODE
CEAB	OEAB	LEAB	CLKAB	Α	В	MODE
Х	Н	Χ	Χ	Χ	Z	Isolation
L	L	L	H or L	Χ	В ₀ ‡ В ₀ §	Latched storage of A data
L	L	L	H or L	Χ	В ₀ §	Latched Storage of A data
Х	L	Н	Х	L	L	Transparent
Х	L	Н	Χ	Н	Н	Transparent
L	L	L	\uparrow	L	L	Clacked storage of A data
L	L	L	\uparrow	Н	Н	Clocked storage of A data
Н	L	L	Χ	Χ	В ₀ §	Clock inhibit

[†] A-to-B data flow is shown. B-to-A data flow is similar, but uses $\overline{\text{OEBA}}$, LEBA, CLKBA, and $\overline{\text{CEBA}}$.

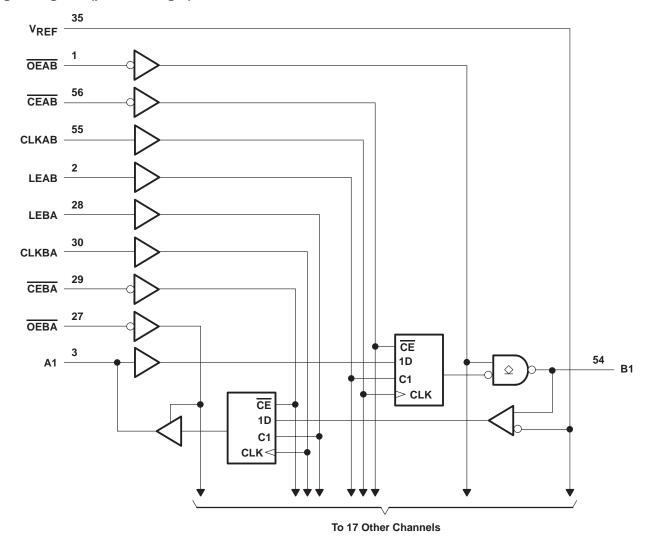


[‡] Output level before the indicated steady-state input conditions were established, provided that CLKAB was high before LEAB went low.

[§] Output level before the indicated steady-state input conditions were established.

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logic diagram (positive logic)



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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V _{CC} : 3.3 V	
Input voltage range, V _I (see Note 1): A-port and control inputs	
B port and V _{RFF}	0.5 V to 4.6 V
Voltage range applied to any output in the high or power-off state, V _O	
(see Note 1): A port	–0.5 V to 7 V
B port	
Current into any output in the low state, IO: A port	
B port	
Current into any A-port output in the high state, IO (see Note 2)	64 mA
Continuous current through each V _{CC} or GND	
Input clamp current, I _{IK} (V _I < 0)	
Output clamp current, I _{OK} (V _O < 0)	–50 mA
Package thermal impedance, θ _{JA} (see Note 3): DGG package	
DL package	
Storage temperature range, T _{stg}	–65°C to 150°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
 - 2. This current flows only when the output is in the high state and $V_O > V_{CC}$.
 - 3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Notes 4 through 6)

			MIN	NOM	MAX	UNIT	
Voc	Supply voltage	3.3 V	3.15	3.3	3.45	V	
Vcc	Supply voltage	5 V	4.75	5	5.25]	
\/	Termination voltage	GTL	1.14	1.2	1.26	V	
VTT	remination voltage	GTLP	1.35	1.5	1.65]	
\/	Cumply voltage	GTL	0.74	0.8	0.87	V	
VREF	Supply voltage	GTLP	0.87	1	1.1	1 °	
1/.	Input voltage	B port			VTT	V	
۷į	Input voltage	Except B port			5.5]	
V	I limb lavel input valtage	B port	VREF+50 m\	′		V	
VIH	High-level input voltage	Except B port	2]	
V	Low-level input voltage	B port		\	/ _{REF} -50 mV	V	
VIL	Low-level input voltage	Except B port			0.8]	
lik	Input clamp current	-			-18	mA	
ІОН	High-level output current	A port			-32	mA	
la.	Low lovel output ourrent	A port			64		
IOL	Low-level output current	B port			34	mA	
T _A	Operating free-air temperature	<u>.</u>	-40		85	°C	

NOTES: 4. All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

- 5. Normal connection sequence is GND first, $V_{CC} = 5 \text{ V}$ second, and $V_{CC} = 3.3 \text{ V}$, I/O, control inputs, V_{TT} , and V_{REF} (any order) last.
- V_{TT} and R_{TT} can be adjusted to accommodate backplane impedances as long as they do not exceed the dc absolute I_{OL} ratings. Similarly, V_{REF} can be adjusted to optimize noise margins, but normally is 2/3 V_{TT}.



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electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAM	METER	TER TEST CONDITIONS MIN		MIN	TYP [†]	MAX	UNIT	
VIK		V_{CC} (3.3 V) = 3.15 V, V_{CC} (5 V) = 4.75 V, I_{I} = -18 mA		I _I = -18 mA			-1.2	V
		V _{CC} (3.3 V) = 3.15 V to 3.4 V _{CC} (5 V) = 4.75 V to 5.25		I _{OH} = -100 μA	V _{CC} (3.3 V) -0.2			
VOH	A port	V _{CC} (3.3 V) = 3.15 V,	V _{CC} (5 V) = 4.75 V	I _{OH} = –8 mA	2.4			V
		VCC (3.3 V) = 3.15 V,	vCC (2 v) = 4.75 v	I _{OH} = -32 mA	2			
				I _{OL} = 100 μA			0.2	
	A port	V _{CC} (3.3 V) = 3.15 V,	V _{CC} (5 V) = 4.75 V	I _{OL} = 16 mA			0.4	
VOL	A port	VCC(3.3 V) = 3.13 V,	VCC (5 V) = 4.75 V	I _{OL} = 32 mA			0.5	V
				I _{OL} = 64 mA			0.55	
	B port	V_{CC} (3.3 V) = 3.15 V,	V_{CC} (5 V) = 4.75 V,	I _{OL} = 34 mA			0.65	
	Control inputs	V _{CC} (3.3 V) = 0 or 3.45 V,	V_{CC} (5 V) = 0 or 5.25 V,	V _I = 5.5 V			10	
				V _I = 5.5 V			20	
l _l	A port	V_{CC} (3.3 V) = 3.45 V,	V_{CC} (5 V) = 5.25 V	V _I = V _{CC} (3.3 V)			1	μΑ
•	'			V _I = 0			-30	
	Durant	V (0.010 0.45V V (510 5.05)	\/ (5\\\) 5.05\\/	$V_{I} = V_{CC} (3.3 \text{ V})$			5	
	B port	V_{CC} (3.3 V) = 3.45 V,	V_{CC} (5 V) = 5.25 V	V _I = 0			-5	
I _{off}		$V_{CC} = 0$,	V_{I} or $V_{O} = 0$ to 4.5 V				100	μΑ
				V _I = 0.8 V	75			
I _{I(hold)}	A port	V_{CC} (3.3 V) = 3.15 V,	V_{CC} (5 V) = 4.75 V	V _I = 2 V	– 75			μΑ
, ,				$V_{I} = 0 \text{ to } V_{CC}(3.3 \text{ V})^{\ddagger}$			±500	
1	A port	V _{CC} (3.3 V) = 3.45 V,	V _{CC} (5 V) = 5.25 V,	VO = VCC (3.3 V)			1	^
IOZH	B port	V_{CC} (3.3 V) = 3.45 V,	V _{CC} (5 V) = 5.25 V,	V _O = 1.5 V			10	μΑ
1	A port	V _{CC} (3.3 V) = 3.45 V,	V _{CC} (5 V) = 5.25 V,	V _O = 0			-1	
IOZL	B port	V_{CC} (3.3 V) = 3.45 V,	V _{CC} (5 V) = 5.25 V,	V _O = 0.65 V			-10	μΑ
	l		<i></i>	Outputs high			1	
I _{CC} (3.3 V)	A or B port	V_{CC} (3.3 V) = 3.45 V, V_{CC} V _I = V_{CC} (3.3 V) or GND§,	$(5 \text{ V}) = 5.25 \text{ V}, I_{\text{O}} = 0,$ Vi = VTT or GND¶	Outputs low			5	mA
(3.5 V)	Port	V = VCC (3.5 V) 61 61426,	VI = VII OI OIND"	Outputs disabled			1	
_				Outputs high			120	
ICC (5 V)	A or B	V_{CC} (3.3 V) = 3.45 V, V_{CC} V _I = V_{CC} (3.3 V) or GND§,	$(5 \text{ V}) = 5.25 \text{ V}, I_{\text{O}} = 0,$ V ₁ = V _{TT} or GND¶	Outputs low			120	mA
(0)	Port	1 V = VCC (0.0 V) 01 01420,	V = V 01 014D "	Outputs disabled			120	
ΔI _{CC} (3.3 V)#		V_{CC} (3.3 V) = 3.45 V, V_{CC} (5 V) = 5.25 V, One A-port or control input at 2.7 V, Other A-port or control inputs at V_{CC} (3.3 V) or GND				1	mA	
Ci	Control inputs	V _I = 3.15 V or 0	I = 3.15 V or 0			4		pF
C.	A port	V _O = 3.15 V or 0				8.5		, F
Cio	B port					8	pF	

[†] All typical values are at V_{CC} (3.3 V) = 3.3 V, V_{CC} (5 V) = 5 V, T_A = 25°C.



[‡] This is the bus-hold maximum dynamic current. It is the minimum overdrive current required to switch the input from one state to another.

[§] This is the V_I for A-port or control inputs.

¶ This is the V_I for B port.

[#]This is the increase in supply current for each input that is at the specified TTL voltage level rather than VCC or GND.

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timing requirements over recommended ranges of supply voltage and operating free-air temperature, V_{TT} = 1.5 V and V_{REF} = 1 V for GTLP (unless otherwise noted) (see Figure 2)

			MIN	MAX	UNIT
fclock	Clock frequency			85	MHz
	Pulse duration	LEAB or LEBA high	3.3		
t _W	Pulse duration	CLKAB or CLKBA high or low	5.7		ns
		A before CLKAB↑	1		
		B before CLKBA↑	1.8		
		A before LEAB↓	0.5		ns
t _{SU} Setup time	Setup time	B before LEBA↓	1.2		
		CEAB before CLKAB↑ CEBA before CLKBA↑	1.2		
			1.4		
		A after CLKAB↑	1.9		
		B after CLKBA↑	0.5		
4.	I laid time	A after LEAB↓	2.7		
th Hold time	Hold liftle	B after LEBA↓	3.5		ns
		CEAB after CLKAB↑	1.2		
		CEBA after CLKBA↑	1.1		

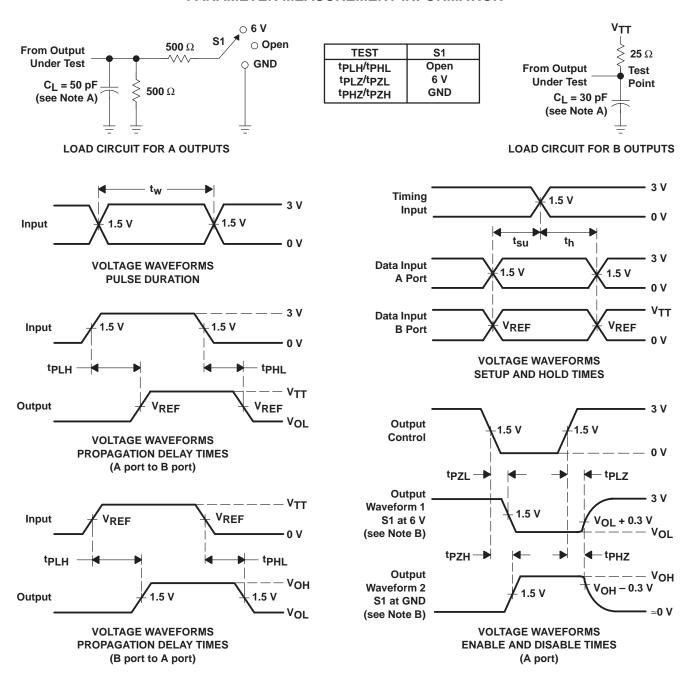
switching characteristics over recommended ranges of supply voltage and operating free-air temperature, V_{TT} = 1.5 V and V_{REF} = 1 V for GTLP (see Figure 2)

	11=1					
PARAMETER	FROM (INPUT)	TO (OUTPUT)	MIN	түр†	MAX	UNIT
f _{max}			85			MHz
	А		2.5		6.9	ns
^t pd	LEAB	В	3.2		7.3	
	CLKAB	3.4		7.8		
t _{en}	<u> </u>	В	2.8		7	20
^t dis	OEAB	В	2.8		7	ns
t _r	Transition time, B ou	utputs (20% to 80%)	2.6		ns	
t _f	Transition time, B outputs (80% to 20%)			2.6		ns
	В		1.5		5.7	
^t pd	LEBA	А	1.8		5.7	ns
•	CLKBA		2.3		5.5	
^t en	 OEBA	Δ.	1.8		6.1	
^t dis	OEBA	A	1.8		6.1	ns

[†] All typical values are at V_{CC} (3.3 V) = 3.3 V, V_{CC} (5 V) = 5 V, T_A = 25°C.



PARAMETER MEASUREMENT INFORMATION



- NOTES: A. C_L includes probe and jig capacitance.
 - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 - C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_Q = 50 \Omega$, $t_f \leq 2.5 \text{ ns.}$
 - D. The outputs are measured one at a time with one transition per measurement.

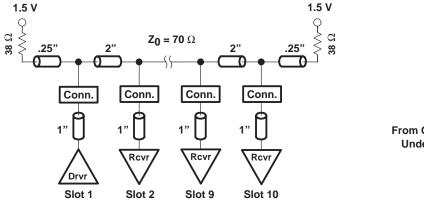
Figure 2. Load Circuits and Voltage Waveforms



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DISTRIBUTED-LOAD BACKPLANE SWITCHING CHARACTERISTICS

The previous switching characteristics table shows the switching characteristics of the device into a lumped load (Figure 2). However, the designer's backplane application most likely is a distributed load, the physical representation as shown in Figure 3. This backplane, or distributed load, can be closely approximated to an RLC circuit, as in Figure 4. This device has been designed for optimum performance into this RLC circuit. The following switching characteristics table shows the switching characteristics of the device into the RLC load, to help the designer better understand the performance of the GTLP device in this typical backplane. See www.ti.com/sc/gtlp for more information.



From Output Under Test $C_L = 9 \text{ pF}$

Figure 3. Medium-Drive Test Backplane

Figure 4. Medium-Drive RLC Network

switching characteristics over recommended ranges of supply voltage and operating free-air temperature, V_{TT} = 1.5 V and V_{REF} = 1 V for GTLP (see Figure 4)[†]

PARAMETER	FROM (INPUT)	TO (OUTPUT)	MIN	түр‡	UNIT
fmax			85		MHz
	А			3.6	ns
^t pd	LEAB	В		4.3	
	CLKAB			4.4	
t _{en}	OEAB	В		4.1	nc
t _{dis}	OEAB	В		4.3	ns
t _r	Rise time, B outputs (20% to 80%)			1.4	ns
t _f	Fall time, B outputs (80% to 20%)			2.1	ns

[†] TI SPICE simulation data



[‡] All typical values are at $V_{CC} = 3.3 \text{ V}$, $T_A = 25^{\circ}\text{C}$.

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